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## MXD8512A

## $0.5 \sim 4.0 \mathrm{GHz}$ SPST Antenna Tuning Switch

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## General Description

The MXD8512A is a CMOS silicon-on-insulator (SOI), single-pole, single-throw (SPST) switch. The high linearity and ruggedness performance and extremely low insertion loss makes the device an ideal choice for GSM/WCDMA/LTE handset antenna tuning application.

The MXD8512A SPST switch is provided in a compact $0.7 \mathrm{~mm} \times 1.1 \mathrm{~mm} \times 0.377 \mathrm{~mm} 6$-lead QFN package. A functional block diagram is shown in Figure 1. The pin configuration and package are shown in Figure 2. Signal pin assignments and functional pin descriptions are provided in Table 1.

Functional Block Diagram and Pin Function

## Applications

- GSM/WCDMA/LTE band and mode switching
- Antenna tuning switch


## Features

- Broadband frequency range: 0.1 to 4.0 GHz
- Low insertion 0.18 dB @ 2.7 GHz
- High P0.1dB of 43.5 dBm
- High Peak Vrf of 50V
- Very Low Ron of 1.2 Ohm
- Very Low Coff of 130fF
- Positive low voltage control: VC = 1.0 to 3.0 $\mathrm{V}, \mathrm{VDD}=1.7$ to 3.3 V , Small, QFN (6-pin, $0.7 \mathrm{~mm} \times 1.1 \mathrm{~mm} \times 0.377 \mathrm{~mm}$ ) package, MSL1

Figure 1.Functional Block Diagram



Figure 2.Pin-out (Top View)

## Application Circuit



Figure 3. MXD8512A Application Circuit

Table 1. Pin Description

| Pin No. | Name | Description | Pin No. | Name | Description |
| :--- | :--- | :--- | :--- | :--- | :--- |
| 1 | RF1 | RF port 1 | 5 | GND | Ground |
| 2 | NC | No connect | 6 | RF2 | RF port 2 |
| 3 | VDD | DC power supply |  |  |  |
| 4 | VC | DC control voltage |  |  |  |

## Truth Table

## Table 2.

| Active Path | VC |
| :---: | :---: |
| RF1 to RF2 OFF | 0 |
| RF1 to RF2 ON | 1 |

Note: "1" $=1.0 \mathrm{~V}$ to 3.00 V . " $0 "=-0 \mathrm{~V}$ to +0.3 V .

## Recommended Operation Range

## Table 3.

| Parameters | Symbol | Min | Typ | Max | Units |
| :--- | :---: | :---: | :---: | :---: | :--- |
| Operation Frequency | $\mathrm{f1}$ | 0.5 | - | 4.0 | GHz |
| Power supply | VDD | 1.7 | 2.8 | 3.3 | V |
| Switch Control Voltage High | $\mathrm{V}_{\text {CTL_H }}$ | 1.0 | 1.8 | 3.0 | V |
| Switch Control Voltage Low | V CTL_L $^{2}$ | 0 | 0 | 0.3 | V |

## Specifications

## Table 4.Electrical Specifications

| Parameter | Symbol | Specification |  |  | Units | Test Condition |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  | Min. | Typical | Max. |  |  |
| DC Specifications |  |  |  |  |  |  |
| Control voltage: <br> Low <br> High | $V_{\text {ctl_L }}$ <br> $V_{\text {cti_h }}$ | $\begin{array}{r} 0 \\ 1.0 \\ \hline \end{array}$ | $\begin{gathered} 0 \\ 1.8 \\ \hline \end{gathered}$ | $\begin{aligned} & 0.3 \\ & 3.0 \\ & \hline \end{aligned}$ | $\begin{aligned} & \mathrm{V} \\ & \mathrm{~V} \end{aligned}$ |  |
| Supply voltage | VDD | 1.7 | 2.8 | 3.3 | V |  |
| Supply current | IDD |  | 100 | 150 | $\mu \mathrm{A}$ | $\mathrm{V}_{\mathrm{DD}}=2.8 \mathrm{~V}$ |
| Control current | $\mathrm{I}_{\text {CTL }}$ |  | 1 | 5 | $\mu \mathrm{A}$ | $\mathrm{V}_{\text {CTL }}=1.8 \mathrm{~V}$ |
| RF Specifications |  |  |  |  |  |  |
| Insertion loss | IL |  | $\begin{aligned} & 0.10 \\ & 0.12 \\ & 0.18 \\ & 0.25 \end{aligned}$ | $\begin{gathered} \hline 0.12 \\ 0.18 \\ 0.25 \\ 0.3 \end{gathered}$ | $\begin{aligned} & \hline \mathrm{dB} \\ & \mathrm{~dB} \\ & \mathrm{~dB} \\ & \mathrm{~dB} \\ & \hline \end{aligned}$ | $\begin{aligned} & 0.5 \text { to } 1.0 \mathrm{GHz} \\ & 1.0 \text { to } 2.2 \mathrm{GHz} \\ & 2.2 \text { to } 3.0 \mathrm{GHz} \\ & 3.0 \text { to } 4.0 \mathrm{GHz} \end{aligned}$ |
| Isolation | ISO | $\begin{aligned} & 25 \\ & 20 \\ & 15 \\ & 14 \\ & \hline \end{aligned}$ | $\begin{aligned} & 28 \\ & 22 \\ & 18 \\ & 17 \\ & \hline \end{aligned}$ |  | $\begin{aligned} & \mathrm{dB} \\ & \mathrm{~dB} \\ & \mathrm{~dB} \\ & \mathrm{~dB} \end{aligned}$ | 0.5 to 1.0 GHz 1.0 to 2.2 GHz 2.2 to 3.0 GHz 3.0 to 4.0 GHz |
| Return loss | $\left\|S_{11}\right\|$ |  | 22 |  | dB | 0.5 to 4.0 GHz |
| On Resistance (RF1/2 to ANT) | Ron |  | 1.2 | 1.4 | $\Omega$ | Switch on Path |
| OFF Capacitance (RF1/2 to ANT) | Coff |  | 130 | 140 | fF | Switch off Path |
| Input 0.1 dB compression point | $\mathrm{P}_{0.1 \mathrm{~dB}}$ |  | +43.5 |  | dBm | 0.5 to 4.0 GHz , ANT to RF1 and RF2 |
| Maximum RF operating voltage | $V_{\text {max }}$ |  | 50 |  | V | $\mathrm{f0}=500$ to 4000 MHz , $25 \%$ duty cycle |
| LTE TX harmonic (RF1/2 to ANT) | $2 f 0$ |  | -110 | -95 | dBm | $\begin{aligned} & \mathrm{fO}=500 \text { to } 4000 \mathrm{MHz}, \mathrm{PIN}=+26 \\ & \mathrm{dBm} \end{aligned}$ |
|  | $3 \mathrm{f0}$ |  | -105 | -85 | dBm |  |
| GSM LB harmonic (RF1/2 to ANT) | $2 f 0$ |  | -60 | -50 | dBm | $\begin{aligned} & \mathrm{fO}=824 \text { to } 915 \mathrm{MHz}, \mathrm{PIN}=+35 \\ & \mathrm{dBm} \end{aligned}$ |
|  | $3 \mathrm{f0}$ |  | -60 | -50 | dBm |  |
| GSM HB harmonic (RF1/2 to ANT) | $2 f 0$ |  | -60 | -50 | dBm | $\text { f0 = } 1710 \text { to } 2690 \mathrm{MHz}, \mathrm{PIN}=+33$ dBm |
|  | $3 \mathrm{f0}$ |  | -60 | -50 | dBm |  |
| Second order intermodulation | IMD2 |  | -115 | -105 | dBm | CW Carrier on RF Port, +20 dBm CW Interferer on ANT port, -15 dBm |
| Third order intermodulation | IMD3 |  | -115 | -105 | dBm | CW Carrier on RF Port, +20 dBm CW Interferer on ANT port, -15 dBm |
| Switching on time |  |  | 5 | 10 | $\mu \mathrm{s}$ | 50\% VCTL to 90\% RF |
| Switching off time |  |  | 5 | 10 | $\mu \mathrm{s}$ | 50\% VCTL to 10\% RF |
| Startup time |  |  | 15 | 30 | $\mu \mathrm{s}$ | Power off state to any RF switch state |

Table 5. IMD2 Test Conditions

| Band | In-band freq | CW Carrier |  | CW Interferer |  |
| :--- | :---: | :---: | :---: | :---: | :---: |
|  | $\mathbf{M H z}$ | $\mathbf{M H z}$ | $\mathbf{d B m}$ | $\mathbf{M H z}$ | $\mathbf{d B m}$ |
| 1 Low | 2140 | 1950 | +20 | 190 | -15 |
| 1 High | 2140 | 1950 | +20 | 4090 | -15 |
| 5 Low | 881.5 | 836.5 | +20 | 45 | -15 |
| 5 High | 881.5 | 836.5 | +20 | 1718 | -15 |

Table 6. IMD3 Test Conditions

| Band | In-band freq | CW Carrier |  | CW Interferer |  |
| :--- | :---: | :---: | :---: | :---: | :---: |
|  | $\mathbf{M H z}$ | $\mathbf{M H z}$ | $\mathbf{d B m}$ | $\mathbf{M H z}$ | $\mathbf{d B m}$ |
| 1 | 2140 | 1950 | +20 | 1760 | -15 |
| 5 | 881.5 | 836.5 | +20 | 791.5 | -15 |

## Absolute Maximum Ratings

Table 7. Maximum ratings

| Parameters | Symbol | Minimum | Maximum | Units |
| :--- | :---: | :---: | :---: | :---: |
| Supply voltage | V |  | +3.6 | V |
| Digital control voltage | VCTL | 0 | +3.3 | V |
| RF input power CW (50 Ohm) | PIN |  | +40 | dBm |
| Operating temperature | Top | -35 | +90 | ${ }^{\circ} \mathrm{C}$ |
| Storage temperature | TSTG | -55 | 150 | ${ }^{\circ} \mathrm{C}$ |
| Electrostatic Discharge <br> Human body model (HBM), <br> Class 1C <br> Machine Model (MM), <br> Class A <br> Charged device model (CDM), <br> Class III $\mathrm{ESD} \mathrm{\_HBM}$ |  | 1000 |  |  |

Note: Exposure to maximum rating conditions for extended periods may reduce device reliability. There is no damage to device with only one parameter set at the limit and all other parameters set at or below their nominal value. Exceeding any of the limits listed here may result in permanent damage to the device.

## Package Outline Dimension



Figure 4. Package outline dimension

Reflow Chart


Figure 7. Recommended Lead-Free Reflow Profile
Table 8.

| Profile Parameter | Lead-Free Assembly, Convection, IR/Convection |
| :---: | :---: |
| Ramp-up rate ( $\mathrm{TS}_{\text {max }}$ to $\mathrm{T}_{\mathrm{p}}$ ) | $3^{\circ} \mathrm{C} /$ second max. |
| Preheat temperature ( $\mathrm{TS}_{\text {min }}$ to $\mathrm{TS}_{\text {max }}$ ) | $150{ }^{\circ} \mathrm{C}$ to $200^{\circ} \mathrm{C}$ |
| Preheat time ( $\mathrm{ts}_{\text {s }}$ ) | 60-180 seconds |
| Time above TL, $217{ }^{\circ} \mathrm{C}$ ( $\mathrm{t}_{\mathrm{L}}$ ) | 60-150 seconds |
| Peak temperature ( $\mathrm{T}_{\mathrm{p}}$ ) | $260{ }^{\circ} \mathrm{C}$ |
| Time within $5^{\circ} \mathrm{C}$ of peak temperature( $\mathrm{tp}^{\text {) }}$ | 20-40 seconds |
| Ramp-down rate | $6^{\circ} \mathrm{C} /$ second max. |
| Time $25^{\circ} \mathrm{C}$ to peak temperature | 8 minutes max. |

## ESD Sensitivity

Integrated circuits are ESD sensitive and can be damaged by static electric charge. Proper ESD protection techniques should be used when handling these devices.

## RoHS Compliant

This product does not contain lead, mercury, cadmium, hexavalent chromium, polybrominated biphenyls (PBB) and polybrominated diphenyl ethers (PBDE), and are considered RoHS compliant.

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